

# Xiangjian Meng

## List of Publications by Year in descending order

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128  
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4,575  
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94433

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110387

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130  
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130  
docs citations

130  
times ranked

5654  
citing authors

#	ARTICLE	IF	CITATIONS
1	Epitaxial growth and phase evolution of ferroelectric La-doped HfO <sub>2</sub> films. Applied Physics Letters, 2022, 120, .	3.3	7
2	HgCdTe/black phosphorus van der Waals heterojunction for high-performance polarization-sensitive midwave infrared photodetector. Science Advances, 2022, 8, eabn1811.	10.3	50
3	End-Bonded Contacts of Tellurium Transistors. ACS Applied Materials & Interfaces, 2021, 13, 7766-7772.	8.0	12
4	Ferroelectric Synaptic Transistor Network for Associative Memory. Advanced Electronic Materials, 2021, 7, 2001276.	5.1	52
5	Gate-Tunable Photodiodes Based on Mixed-Dimensional Te/MoTe <sub>2</sub> Van der Waals Heterojunctions. Advanced Electronic Materials, 2021, 7, 2001066.	5.1	29
6	Interface engineering of ferroelectric-gated MoS <sub>2</sub> phototransistor. Science China Information Sciences, 2021, 64, 1.	4.3	10
7	The Influence Mechanism of Temperature and Storage Period on Polarization Properties of Poly (Vinylidene Fluoride-Trifluoroethylene) Ultrathin Films. Membranes, 2021, 11, 301.	3.0	2
8	Ferroelectric-tuned van der Waals heterojunction with band alignment evolution. Nature Communications, 2021, 12, 4030.	12.8	79
9	Hybrid System Combining Two-Dimensional Materials and Ferroelectrics and Its Application in Photodetection. ACS Nano, 2021, 15, 10982-11013.	14.6	52
10	Functionalities enhancement by an anisotropic strain competition. Ferroelectrics, 2021, 583, 264-277.	0.6	0
11	Ultrasensitive negative capacitance phototransistors. Nature Communications, 2020, 11, 101.	12.8	124
12	Ferroelectricity and antiferromagnetism in organic-inorganic hybrid (1,4-bis(imidazol-1-ylmethyl)benzene)CuCl <sub>4</sub> ·H <sub>2</sub> O. CrystEngComm, 2020, 22, 587-592.	2.6	9
13	Toward a Reliable Synaptic Simulation Using Al-Doped HfO <sub>2</sub> RRAM. ACS Applied Materials & Interfaces, 2020, 12, 10648-10656.	8.0	80
14	Highly Sensitive InSb Nanosheets Infrared Photodetector Passivated by Ferroelectric Polymer. Advanced Functional Materials, 2020, 30, 2006156.	14.9	41
15	A versatile photodetector assisted by photovoltaic and bolometric effects. Light: Science and Applications, 2020, 9, 160.	16.6	56
16	MoTe <sub>2</sub> p-n Homojunctions Defined by Ferroelectric Polarization. Advanced Materials, 2020, 32, e1907937.	21.0	115
17	Two-dimensional series connected photovoltaic cells defined by ferroelectric domains. Applied Physics Letters, 2020, 116, .	3.3	10
18	Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. Nature Electronics, 2020, 3, 43-50.	26.0	167

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19	Extremely Low Dark Current MoS <sub>2</sub> Photodetector via 2D Halide Perovskite as the Electron Reservoir. <i>Advanced Optical Materials</i> , 2020, 8, 1901402.	7.3	55
20	Multifunctional MoS <sub>2</sub> Transistors with Electrolyte Gel Gating. <i>Small</i> , 2020, 16, e2000420.	10.0	23
21	Ultrabroad-Spectrum Photodetectors: Multimechanism Synergistic Photodetectors with Ultrabroad Spectrum Response from 375 nm to 10 Åµm (Adv. Sci. 15/2019). <i>Advanced Science</i> , 2019, 6, 1970089.	11.2	2
22	Efficient two-terminal artificial synapse based on a network of functionalized conducting polymer nanowires. <i>Journal of Materials Chemistry C</i> , 2019, 7, 9933-9938.	5.5	32
23	Ferroelectric properties of gradient doped Y2O3:HfO2 thin films grown by pulsed laser deposition. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	9
24	A study on ionic gated MoS <sub>2</sub> phototransistors. <i>Science China Information Sciences</i> , 2019, 62, 1.	4.3	8
25	A gate-free MoS <sub>2</sub> phototransistor assisted by ferroelectrics. <i>Journal of Semiconductors</i> , 2019, 40, 092002.	3.7	10
26	Multimode Signal Processor Unit Based on the Ambipolar WSe <sub>2</sub> Cr Schottky Junction. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 38895-38901.	8.0	3
27	Tuning the Crystal Structure and Luminescence of Pyrrolidinium Manganese Halides via Halide Ions. <i>Crystal Research and Technology</i> , 2019, 54, 1800236.	1.3	30
28	Ultrasensitive Hybrid MoS <sub>2</sub> ZnCdSe Quantum Dot Photodetectors with High Gain. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 23667-23672.	8.0	62
29	Large-area high quality PtSe <sub>2</sub> thin film with versatile polarity. <i>Informa-Ån-Å-Materi-Åily</i> , 2019, 1, 260-267.	17.3	54
30	Interface-engineered reliable HfO <sub>2</sub> -based RRAM for synaptic simulation. <i>Journal of Materials Chemistry C</i> , 2019, 7, 12682-12687.	5.5	60
31	A Robust Artificial Synapse Based on Organic Ferroelectric Polymer. <i>Advanced Electronic Materials</i> , 2019, 5, 1800600.	5.1	129
32	Ferroelectric Synapses: A Robust Artificial Synapse Based on Organic Ferroelectric Polymer (Adv.) <i>Tj ETQq0 0 0 rgBTj/Overlock 10 Tf 50 2</i>	3.1	3
33	Structural, electrical and magnetic properties of (110)-oriented BF-BZT-ST Films. <i>Ceramics International</i> , 2018, 44, 9053-9057.	4.8	2
34	Optoelectronics: High-performance Photovoltaic Detector Based on MoTe <sub>2</sub> /MoS <sub>2</sub> Van der Waals Heterostructure (Small 9/2018). <i>Small</i> , 2018, 14, 1870038.	10.0	7
35	High-performance Photovoltaic Detector Based on MoTe <sub>2</sub> /MoS <sub>2</sub> Van der Waals Heterostructure. <i>Small</i> , 2018, 14, 1703293.	10.0	205
36	Field Effect Transistors: Ferroelectric Negative Capacitance Field Effect Transistor (Adv. Electron.) <i>Tj ETQq0 0 0 rgBTj/Overlock 10 Tf 50 6</i>	5.1	7

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37	High-performance lead-free two-dimensional perovskite photo transistors assisted by ferroelectric dielectrics. <i>Journal of Materials Chemistry C</i> , 2018, 6, 12714-12720.	5.5	39
38	Spatial and Frequency Selective Plasmonic Metasurface for Long Wavelength Infrared Spectral Region. <i>Advanced Optical Materials</i> , 2018, 6, 1800337.	7.3	23
39	Ferroelectric Negative Capacitance Field Effect Transistor. <i>Advanced Electronic Materials</i> , 2018, 4, 1800231.	5.1	105
40	Photo-induced ferroelectric switching in perovskite CH <sub>3</sub> NH <sub>3</sub> Pb <sub>3</sub> films. <i>Nanoscale</i> , 2017, 9, 3806-3817.	5.6	86
41	Ferroelectric FET for nonvolatile memory application with two-dimensional MoSe <sub>2</sub> channels. <i>2D Materials</i> , 2017, 4, 025036.	4.4	85
42	Photoexcited terahertz conductivity dynamics of graphene tuned by oxygen-adsorption. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	22
43	Preparation of La <sub>0.67</sub> Ca <sub>0.23</sub> Sr <sub>0.1</sub> MnO <sub>3</sub> thin films with interesting electrical and magnetic properties via pulsed-laser deposition. <i>Science China: Physics, Mechanics and Astronomy</i> , 2017, 60, 1.	5.1	3
44	Two-dimensional negative capacitance transistor with polyvinylidene fluoride-based ferroelectric polymer gating. <i>Npj 2D Materials and Applications</i> , 2017, 1, .	7.9	77
45	Giant negative electrocaloric effect in PbZrO <sub>3</sub> /0.88BaTiO <sub>3</sub> ∞0.12Bi(Mg <sub>1/2</sub> ,Ti <sub>1/2</sub> )O <sub>3</sub> multilayered composite ferroelectric thin film for solid-state refrigeration. <i>Journal of Applied Physics</i> , 2017, 122, .	2.5	10
46	Electrical characterization of MoS <sub>2</sub> field-effect transistors with different dielectric polymer gate. <i>AIP Advances</i> , 2017, 7, .	1.3	15
47	Ferroelectric polymer tuned two dimensional layered MoTe <sub>2</sub> photodetector. <i>RSC Advances</i> , 2016, 6, 87416-87421.	3.6	51
48	Visible to short wavelength infrared In <sub>2</sub> Se <sub>3</sub> -nanoflake photodetector gated by a ferroelectric polymer. <i>Nanotechnology</i> , 2016, 27, 364002.	2.6	63
49	Optoelectronic Properties of Few-Layer MoS <sub>2</sub> FET Gated by Ferroelectric Relaxor Polymer. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 32083-32088.	8.0	76
50	Tunnel electroresistance through organic ferroelectrics. <i>Nature Communications</i> , 2016, 7, 11502.	12.8	104
51	Electrical and mechanical switching of ferroelectric polarization in the 70 nm BiFeO <sub>3</sub> film. <i>Scientific Reports</i> , 2016, 6, 19092.	3.3	28
52	Flexible graphene field effect transistor with ferroelectric polymer gate. <i>Optical and Quantum Electronics</i> , 2016, 48, 1.	3.3	21
53	When Nanowires Meet Ultrahigh Ferroelectric Field∞High-Performance Full-Depleted Nanowire Photodetectors. <i>Nano Letters</i> , 2016, 16, 2548-2555.	9.1	135
54	Photodetectors: Ultrasensitive and Broadband MoS <sub>2</sub> Photodetector Driven by Ferroelectrics ( <i>Adv. Mater.</i> 42/2015). <i>Advanced Materials</i> , 2015, 27, 6538-6538.	21.0	8

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55	Antiferroelectric Thin Films: Giant Negative Electrocaloric Effect in Antiferroelectric La-Doped Pb(ZrTi)O <sub>3</sub> Thin Films Near Room Temperature (Adv. Mater. 20/2015). Advanced Materials, 2015, 27, 3164-3164.	21.0	3
56	Homogeneous switching mechanism in pure polyvinylidene fluoride ultrathin films. Physical Review B, 2015, 92, .	3.2	11
57	Ultrasensitive and Broadband MoS <sub>2</sub> Photodetector Driven by Ferroelectrics. Advanced Materials, 2015, 27, 6575-6581.	21.0	722
58	Properties of Tunability and Stored Energy Density in the Ferroelectric Multilayers. Ferroelectrics, 2015, 488, 112-118.	0.6	0
59	Diffuse Phase Transition and Relaxor-Like Behavior in P(VDF-TrFE-CFE) Films Irradiated with Different Electron Dose. Ferroelectrics, 2015, 488, 140-147.	0.6	1
60	Bent Deformation's Impact on Ferroelectric and Pyroelectric Properties of the P(VDF-TrFE) Thin Films. Ferroelectrics, 2015, 488, 154-161.	0.6	1
61	Ferroelectric control of magnetism in P(VDF-TrFE)/Co heterostructure. Journal of Materials Science: Materials in Electronics, 2015, 26, 7502-7506.	2.2	9
62	Effects of Electron Irradiation on the Dielectric Behavior of Langmuir-Blodgett Terpolymer Films. Ferroelectrics, 2015, 478, 81-87.	0.6	1
63	Giant Negative Electrocaloric Effect in Antiferroelectric La-Doped Pb(ZrTi)O <sub>3</sub> Thin Films Near Room Temperature. Advanced Materials, 2015, 27, 3165-3169.	21.0	241
64	$\beta$ phase instability in poly(vinylidene fluoride/trifluoroethylene) thin films near $\beta$ relaxation temperature. Applied Physics Letters, 2015, 106, .	3.3	12
65	Temperature-dependent lattice dynamics and electronic transitions in $P_{0.93}B_{0.07}Zn$ Physical Review B, 2015, 91, .	3.2	23
66	Pyromellitic Diimide-Benzodithiophene Copolymer for Polymer Solar Cells: Effect of Side Chain Length and Thiophene $\pi$ -Bridge on Optical and Electronic Properties. Molecular Crystals and Liquid Crystals, 2014, 604, 151-163.	0.9	2
67	Enhanced dielectric and ferroelectric properties in the artificial polymer multilayers. Applied Physics Letters, 2014, 104, .	3.3	12
68	Transition of the polarization switching from extrinsic to intrinsic in the ultrathin polyvinylidene fluoride homopolymer films. Applied Physics Letters, 2014, 104, .	3.3	46
69	Electronic structure and optical responses of nanocrystalline BiGaO <sub>3</sub> films: A combination study of experiment and theory. Journal of Applied Physics, 2014, 115, .	2.5	7
70	Evolution of multiple dielectric responses and relaxor-like behaviors in pure and nitrogen-ion-implanted (Ba, Sr)TiO <sub>3</sub> thin films. Applied Physics Letters, 2014, 104, .	3.3	12
71	Ferroelectric switching of elastin. Proceedings of the National Academy of Sciences of the United States of America, 2014, 111, E2780-6.	7.1	66
72	Above-room-temperature molecular ferroelectric and fast switchable dielectric of diisopropylammonium perchlorate. Journal of Materials Chemistry C, 2014, 2, 9957-9963.	5.5	53

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73	Design and synthesis of pyromellitic diimide-based donor-acceptor conjugated polymers for photovoltaic application. <i>Polymers for Advanced Technologies</i> , 2014, 25, 809-815.	3.2	1
74	Synthetically controlling the optoelectronic properties of dithieno[2,3-d:2',3'-d']benzo[1,2-b:4,5-b']dithiophene-alt-diketopyrrolopyrrole-conjugated polymers for efficient solar cells. <i>Journal of Materials Chemistry A</i> , 2014, 2, 15316-15325.	10.3	46
75	Enhanced ferroelectric and dielectric properties of the P(VDF-TrFE)/Ag nanoparticles composite thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 3461-3465.	2.2	11
76	Abnormal polarization switching of relaxor terpolymer films at low temperatures. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	17
77	The Cr-substitution concentration dependence of the structural, electric and magnetic behaviors for Aurivillius Bi <sub>5</sub> Ti <sub>3</sub> FeO <sub>15</sub> multiferroic ceramics. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	41
78	Unipolar poling-induced high switching speed and improved imprint behaviors for poly(vinylidene fluoride)/terpolymer capacitors. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	10
79	Processing optimization and sintering time dependent magnetic and optical behaviors of Aurivillius Bi <sub>5</sub> Ti <sub>3</sub> FeO <sub>15</sub> ceramics. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	43
80	The creep process of the domain switching in poly(vinylidene fluoride-trifluoroethylene) ferroelectric thin films. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	13
81	Small polaron migration associated multiple dielectric responses of multiferroic DyMnO <sub>3</sub> polycrystal in low temperature region. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	29
82	Low-temperature processing of high-performance 0.74Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -0.26PbTiO <sub>3</sub> buffered thin films on La <sub>0.6</sub> Sr <sub>0.4</sub> CoO <sub>3</sub> substrates for pyroelectric arrays applications. <i>Journal of the American Ceramic Society</i> , 2012, 95, 1367-1371.	3.8	14
83	Self-assembly of reduced graphene oxide at liquid-air interface for organic field-effect transistors. <i>Journal of Materials Chemistry</i> , 2012, 22, 6171.	6.7	12
84	Dielectric responses and scaling behaviors in Aurivillius Bi <sub>6</sub> Ti <sub>3</sub> Fe <sub>2</sub> O <sub>18</sub> multiferroic thin films. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	75
85	Competing conduction mechanisms of two-dimensional electrons and bulk-like electrons in the n-type surface of the naturally oxidized p-type HgCdTe thin film. <i>Applied Physics A: Materials Science and Processing</i> , 2012, 106, 703-707.	2.3	0
86	Enhanced Physical Properties of Ferroelectric Poly(Vinylidene Fluoride Trifluoroethylene) Copolymer Capacitor with Ni/Fe Electrodes. <i>Ferroelectrics</i> , 2011, 423, 141-149.	0.6	0
87	Relationships Between Ac Dielectric Nonlinearities and Molecular Conformations in Ferroelectric Langmuir-Blodgett Polymer Films. <i>Ferroelectrics</i> , 2011, 423, 150-156.	0.6	0
88	Ferroelectricity of ultrathin ferroelectric Langmuir-Blodgett polymer films on conductive LaNiO <sub>3</sub> electrodes. <i>Materials Letters</i> , 2011, 65, 1989-1991.	2.6	6
89	Structure and dielectric properties of 80%Pb(Zn <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -20%PbTiO <sub>3</sub> thin films prepared by modified sol-gel process. <i>Journal of Sol-Gel Science and Technology</i> , 2011, 60, 164-169.	2.4	1
90	Aging-induced abnormality of dielectric response under dc bias in Ba(Zr, Ti)O <sub>3</sub> thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2011, 104, 123-128.	2.3	14

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91	Fabrication and properties of solution processed all polymer thin film ferroelectric device. Journal of Applied Polymer Science, 2011, 120, 1510-1513.	2.6	24
92	The preparation and ferroelectric properties of defect-free ultrathin films of vinylidene fluoride oligomer. Journal of Applied Physics, 2010, 107, 034101.	2.5	14
93	Magnetic Field Induced Dielectric and Ferroelectric Behaviors in Pb(Zr <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> /CoFe <sub>2</sub> O <sub>4</sub> -3 Thick Composite Films. Ferroelectrics, 2010, 410, 50-58.	0.6	2
94	STRUCTURES AND PROPERTIES OF PZT(52/48) THIN FILMS WITH DIFFERENT SUBSTRATE TEMPERATURE AND OXYGEN PERCENTAGE IN MIXED Ar AND O <sub>2</sub> GAS ON LNO/Si (100) BY SPUTTERING. Integrated Ferroelectrics, 2010, 113, 63-71.	0.7	1
95	EFFECT OF SPUTTERING WORKING PRESSURE ON MICROSTRUCTURES AND PROPERTIES OF PZT THIN FILMS. Integrated Ferroelectrics, 2010, 113, 31-40.	0.7	3
96	Structure Change of Poly(Vinylidene Fluoride-Trifluoroethylene) Ferroelectric Thin Films on Different Electrodes. Ferroelectrics, 2010, 405, 183-187.	0.6	0
97	The Optical Dispersion of Langmuir-Blodgett Terpolymer Films. Ferroelectrics, 2010, 405, 120-125.	0.6	3
98	A Sharp Peak of the Differential Conductivity of P(VDF-TrFe) Films Near the Coercive Field. Ferroelectrics, 2010, 405, 133-137.	0.6	0
99	The Ferroelectric Properties and the Ultraviolet-Near Infrared Optical Response of 0.5 mol% Mn Doped (Pb, Sr)TiO <sub>3</sub> Thin Films. Ferroelectrics, 2010, 411, 9-14.	0.6	1
100	Temperature dependent optical properties of Mn doped (Pb,Sr)TiO <sub>3</sub> ferroelectric films in absorption region: Electron-phonon interaction. Journal of Applied Physics, 2010, 108, 114102.	2.5	20
101	Domain stabilization effect of interlayer on ferroelectric poly(vinylidene fluoride-trifluoroethylene) copolymer ultrathin film. Journal of Applied Physics, 2009, 105, .	2.5	46
102	Effects of Mn doping on dielectric and ferroelectric properties of (Pb,Sr)TiO <sub>3</sub> films on (111) Pt/Ti/SiO <sub>2</sub> /Si substrates. Journal of Applied Physics, 2009, 106, .	2.5	20
103	Effect of in-plane misfit strains on dielectric and pyroelectric response of poly(vinylidene) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 5	2.5	12
104	The Debye-like relaxation mechanism in poly(vinylidene fluoride-trifluoroethylene) ferroelectric polymers. Journal of Applied Physics, 2009, 106, 104113.	2.5	0
105	Effect of oxygen to argon ratio on properties of (Ba,Sr)TiO <sub>3</sub> thin films prepared on LaNiO <sub>3</sub> /Si substrates. Journal of Applied Physics, 2009, 105, 061637.	2.5	7
106	The effect of ac field amplitude on the relaxor behaviors in Langmuir-Blodgett terpolymer films. Journal of Applied Physics, 2009, 106, .	2.5	8
107	Highly Temperature Stable Dielectric Properties of Nanograin Barium Strontium Titanate Thin Films Grown on Silicon Substrate. Journal of the American Ceramic Society, 2009, 92, 2795-2797.	3.8	3
108	Threshold fields in the dc bias dependence of dielectric responses of relaxor ferroelectric terpolymer films. Journal of Applied Physics, 2009, 106, 104102.	2.5	7

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109	Effect of Fe-doping concentration on microstructure, electrical, and magnetic properties of Pb(Zr <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> thin films prepared by chemical solution deposition. Journal of Applied Physics, 2009, 106, .	2.5	26
110	Evolution of electric field amplitude dependent scaling behaviors in ferroelectric films over a broad temperature range. Applied Physics Letters, 2008, 93, .	3.3	16
111	Hopping conduction and low-frequency dielectric relaxation in 5mol% Mn doped (Pb,Sr)TiO <sub>3</sub> films. Journal of Applied Physics, 2008, 104, .	2.5	47
112	High electric tunability of relaxor ferroelectric Langmuir-Blodgett terpolymer films. Applied Physics Letters, 2008, 93, 192905.	3.3	33
113	Study on the Ferroelectric Thin Films for Uncooled Infrared Detection. Ferroelectrics, 2007, 352, 12-24.	0.6	5
114	Electric field induced conversion in the nature of the phase transition from the first order to the second order for Langmuir-Boldgett polymer films. Applied Physics Letters, 2007, 91, .	3.3	9
115	LOW-TEMPERATURE PREPARATION OF Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> THIN FILM. Integrated Ferroelectrics, 2006, 81, 123-128.	0.7	3
116	Electrical and optical properties of Pb(Mg <sub>1-x</sub> Nb <sub>2x-3</sub> )O <sub>3</sub> -PbTiO <sub>3</sub> thin films prepared by chemical solution deposition. Applied Physics Letters, 2005, 87, 072903.	3.3	21
117	Low-temperature preparation of highly (100)-oriented Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> thin film by high oxygen-pressure processing. Applied Physics Letters, 2005, 86, 252902.	3.3	33
118	Optical and electrical properties of highly (100)-oriented PbZr <sub>1-x</sub> Ti <sub>x</sub> O <sub>3</sub> thin films on the LaNiO <sub>3</sub> buffer layer. Journal of Applied Physics, 2004, 96, 2792-2799.	2.5	26
119	Spectroscopic-ellipsometry characterization of the interface layer of PbZr <sub>0.40</sub> Ti <sub>0.60</sub> O <sub>3</sub> /LaNiO <sub>3</sub> /Pt multilayer thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1152-1157.	2.1	5
120	Ferroelectricity of weak-polar organic molecules in alternate Langmuir-Blodgett multilayer films. Science Bulletin, 2003, 48, 2176-2179.	1.7	1
121	Temperature dependence of ferroelectric and dielectric properties of PbZr <sub>0.5</sub> Ti <sub>0.5</sub> O <sub>3</sub> thin film based capacitors. Applied Physics Letters, 2002, 81, 4035-4037.	3.3	28
122	Memory properties of metal-ferroelectric-semiconductor structure. Ferroelectrics, 2001, 253, 239-245.	0.6	0
123	Study of Properties of Urea and L-Alanine Didoped Triglycine Sulfate (UrLATGS) Crystals. Journal of Infrared, Millimeter and Terahertz Waves, 2001, 22, 329-334.	0.6	2
124	Infrared optical properties of LaNiO <sub>3</sub> -platinized silicon and PbZr <sub>1-x</sub> Ti <sub>x</sub> O <sub>3</sub> -LaNiO <sub>3</sub> -platinized silicon heterostructures. Applied Physics Letters, 2001, 78, 793-795.	3.3	17
125	Changes in the interface capacitance for fatigued lead-zirconate-titanate capacitors. Applied Physics Letters, 2001, 78, 2548-2550.	3.3	17
126	Title is missing!. Journal of Materials Science Letters, 2000, 19, 1767-1769.	0.5	4



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127	Investigation of interface and bulk fatigue scenarios in sol-gel derived Pb(Zr <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> films by asymmetric field driving. Applied Physics Letters, 2000, 77, 898-900.	3.3	10
128	Optical Properties of Sol-Gel Derived PbTiO <sub>3</sub> and PbZr <sub>1-x</sub> TiO <sub>3</sub> Ferroelectric Thin Films. Materials Research Society Symposia Proceedings, 1998, 541, 723.	0.1	4